Supporting Information

Thickness Optimization of Zn0.9Mg0.1O Nanoparticle Electron Transport Layer for High-Performance Top-Emission Quantum Dot Light-Emitting Diodes

Gyeong-Pil Jang1, Ji-Hun Yang1, Su-Young. Kim1, Young-Bin Chae1, Hyuk-Doo Choi1, Dae-Gyu Moon1 and Chang-Kyo Kim1,\*

**1**Department of Electronic Materials, Devices, and Equipment, Soonchunhyang University, Asan, Chungnam 31538, Republic of Korea

**\***Corresponding Author Email: ckkim1@sch.ac.kr (Chang-Kyo Kim)









Figure S1. Electroluminescence characteristics of QLEDs with a 50 nm-thick Zn0.9Mg0.1O NP ETLs inside the bank enclosure and without bank: (a) Current density curves as a function of voltage, (b) Luminance curves as a function of voltage, (c) current efficiency curves as a function of current density, and electroluminescence spectra of the QLEDs utilizing Zn0.9Mg0.1O NP ETLs